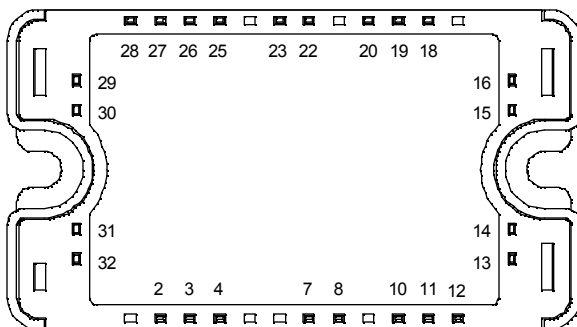
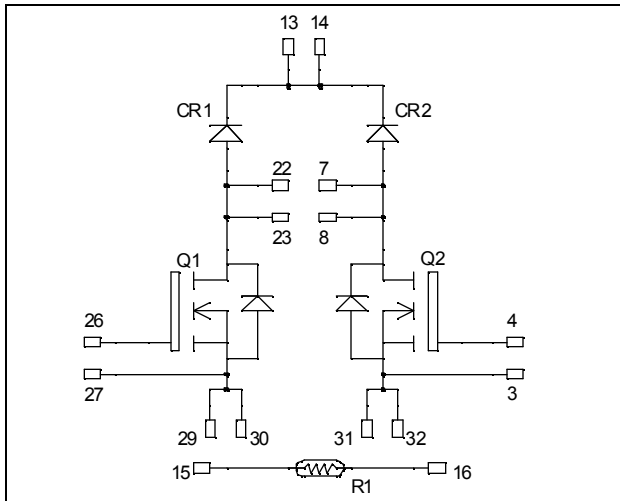


Dual Boost chopper MOSFET Power Module

$V_{DSS} = 500V$

$R_{DSon} = 100m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 37A$ @ $T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	140	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	120	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	37	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	1600	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			100	μA
		$V_{GS} = 0V, V_{DS} = 400V$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 18.5A$		100	120	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		4367		pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		894		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		61		
Q_g	Total gate Charge	$V_{GS} = 10V$		96		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250V$		24		
Q_{gd}	Gate – Drain Charge	$I_D = 37A$		49		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 37A$ $R_G = 5\Omega$		15		ns
T_r	Rise Time			21		
$T_{d(off)}$	Turn-off Delay Time			73		
T_f	Fall Time			52		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 37A, R_G = 5\Omega$		566		μJ
E_{off}	Turn-off Switching Energy			545		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 37A, R_G = 5\Omega$		931		μJ
E_{off}	Turn-off Switching Energy			635		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current		$T_c = 80^\circ\text{C}$	40		A
V_F	Diode Forward Voltage	$I_F = 40A$	$T_j = 25^\circ\text{C}$	1.45		V
			$T_j = 125^\circ\text{C}$	1.35		
t_{rr}	Reverse Recovery Time	$I_F = 40A$ $V_R = 300V$ $di/dt = 2600A/\mu s$	$T_j = 25^\circ\text{C}$	95		ns
			$T_j = 125^\circ\text{C}$	115		
Q_{rr}	Reverse Recovery Charge	$I_F = 40A$ $V_R = 300V$ $di/dt = 2600A/\mu s$	$T_j = 25^\circ\text{C}$	2.6		μC
			$T_j = 125^\circ\text{C}$	4		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		Transistor			0.4	°C/W
			Diode			1.5	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2.5		4.7	N.m
Wt	Package Weight					110	g

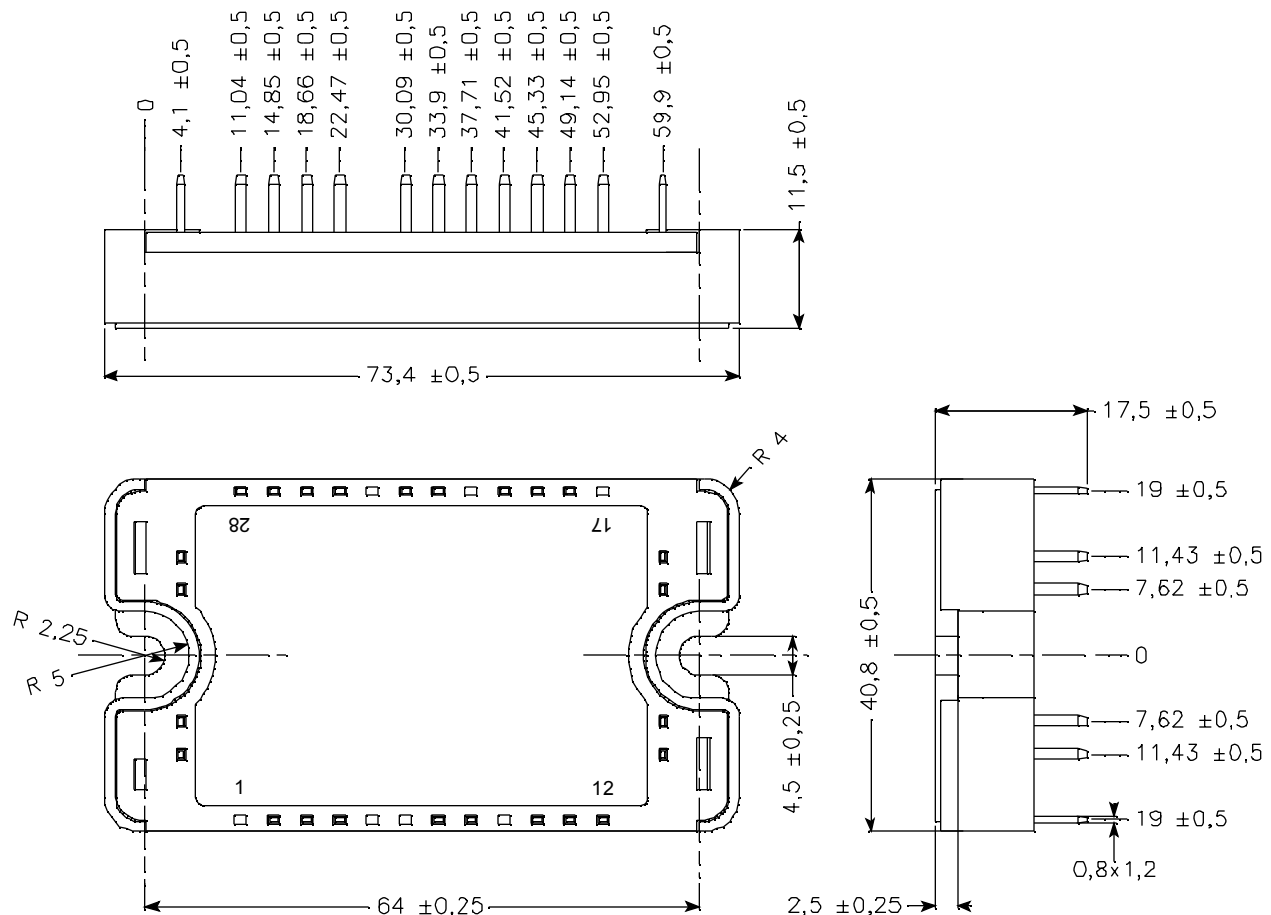
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

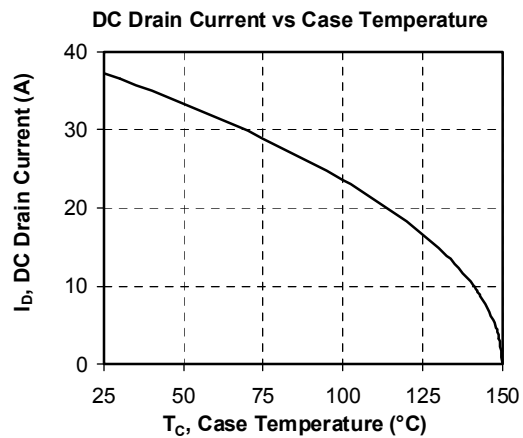
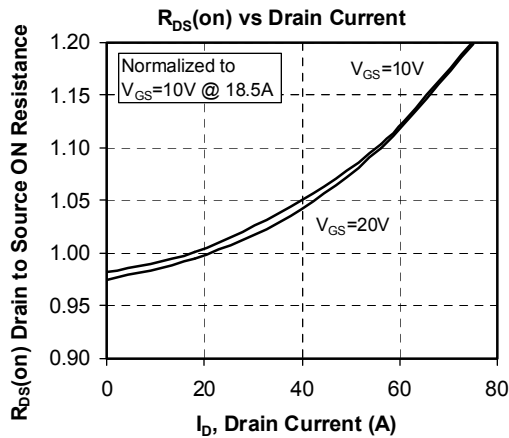
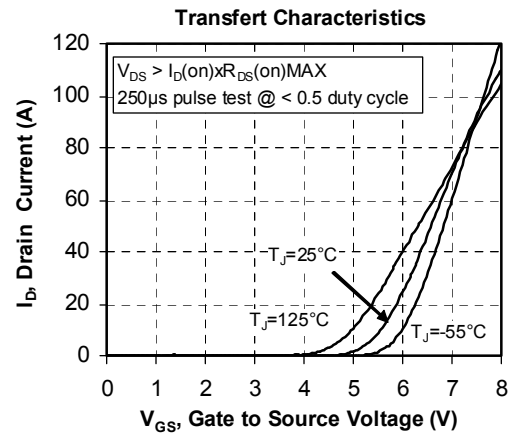
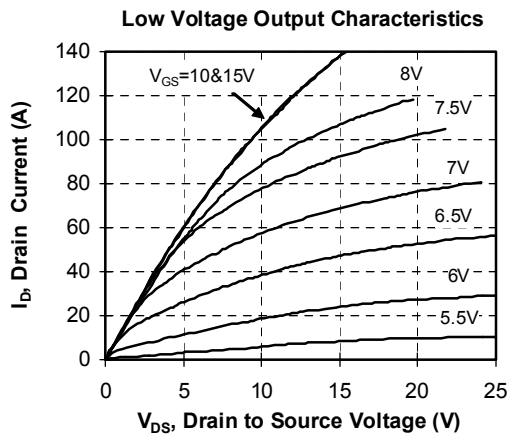
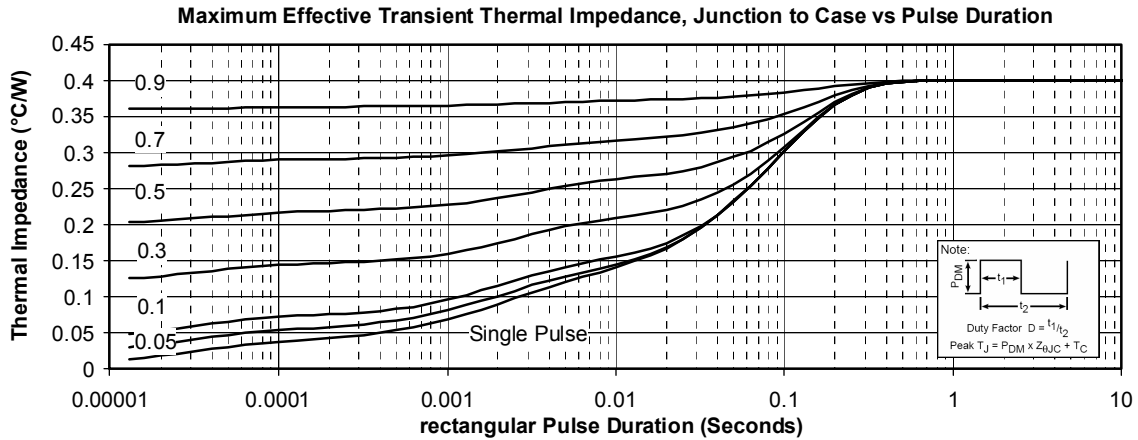
T: Thermistor temperature
R_T: Thermistor value at T

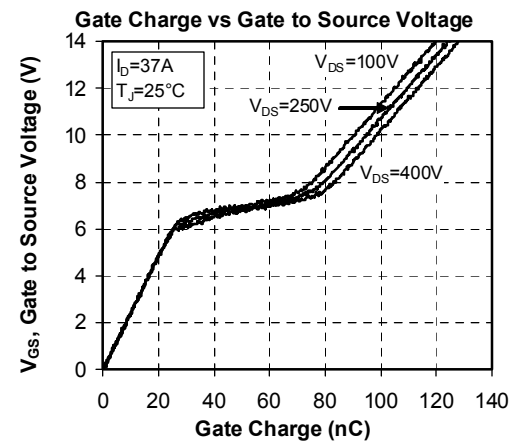
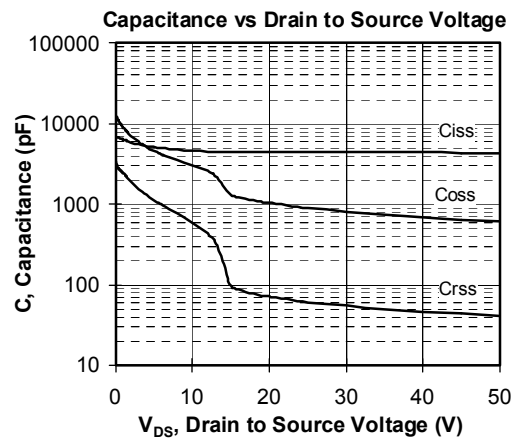
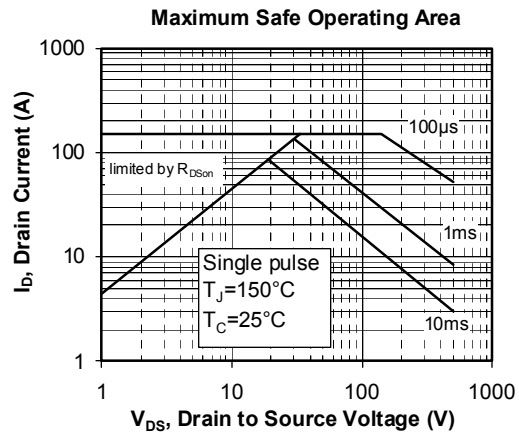
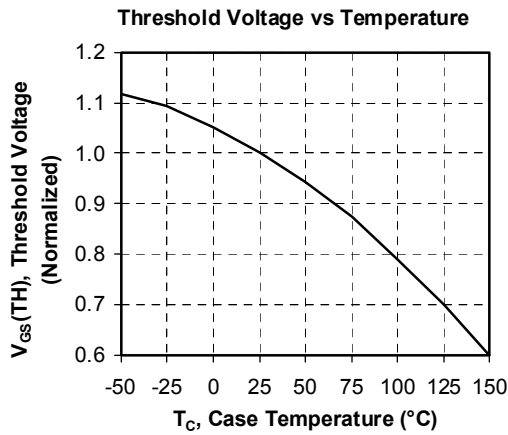
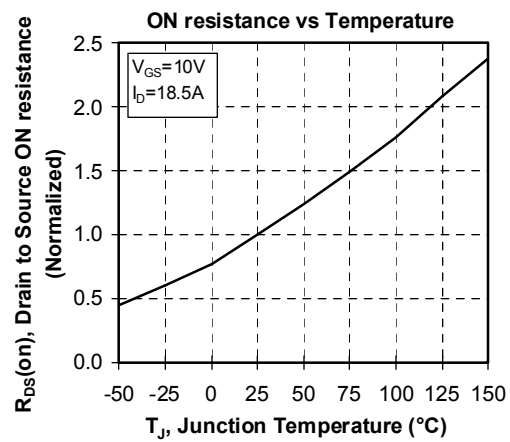
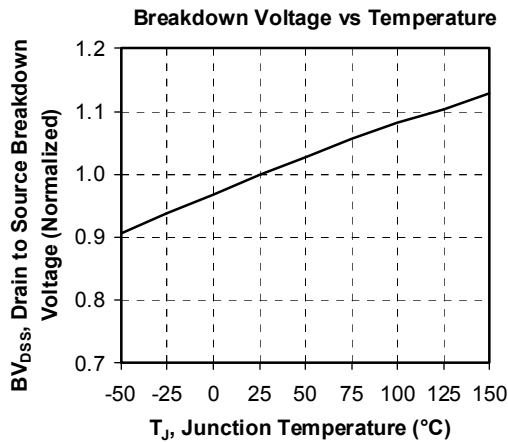
SP3 Package outline (dimensions in mm)

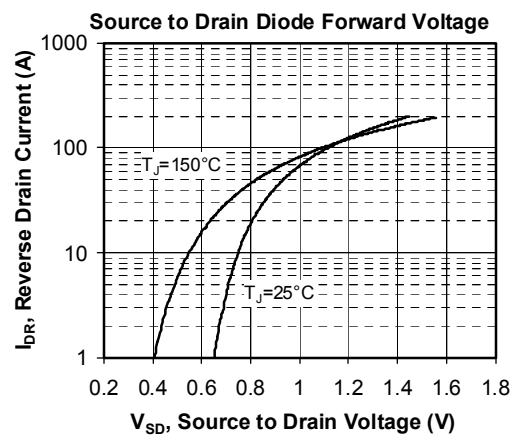
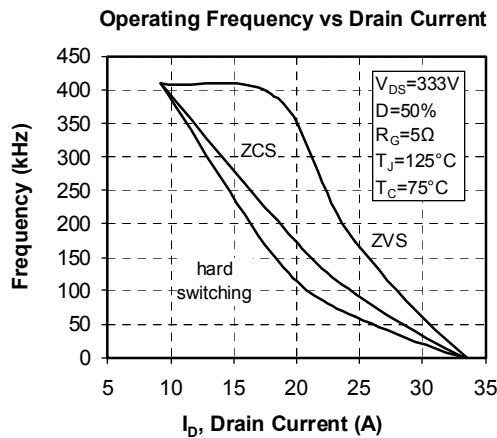
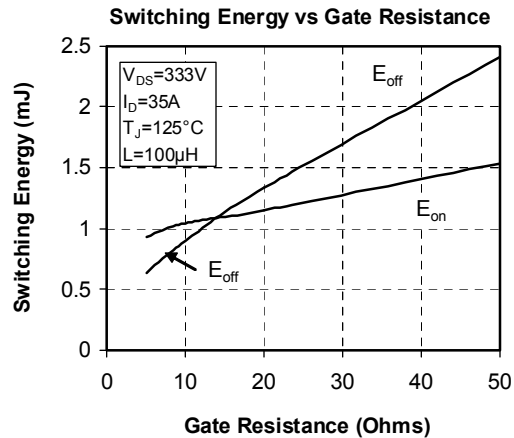
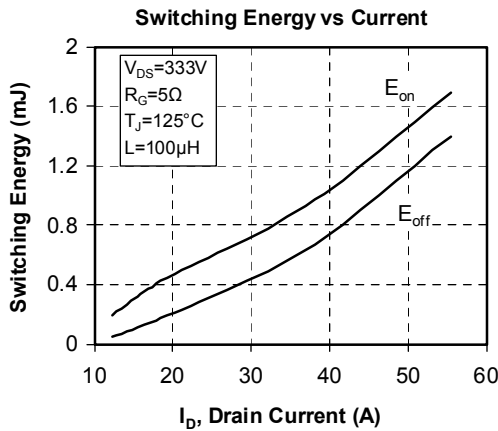
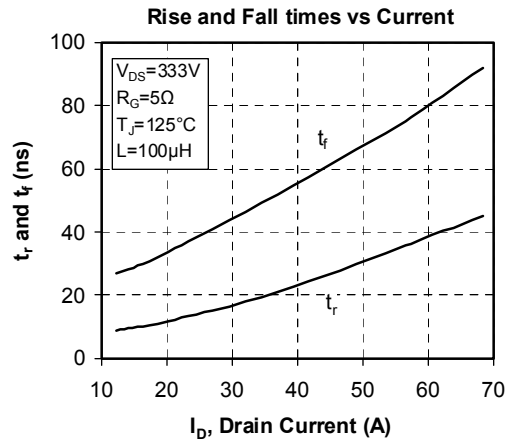
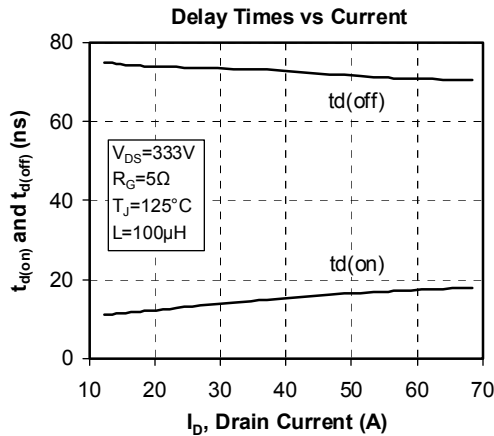


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve







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